






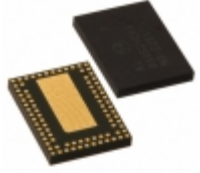



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|---|---|
|  | <h2>SI1022R-T1-GE3</h2> |
| | <p>Hersteller-Teilenummer: SI1022R-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 60V 330MA SC-75A</p> <p>Datenblätter:  SI1022R-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 54367 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|---|---|
| Teilenummer | SI1022R-T1-GE3 |
| Hersteller | Vishay / Siliconix |
| Beschreibung | MOSFET N-CH 60V 330MA SC-75A |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 54367 pcs Stock |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | SC-75A |
| Supplier Device-Gehäuse | SC-75A |
| Verlustleistung (max) | 250mW (Ta) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 60V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 °C | 330mA (Ta) |
| Rds On (Max) @ Id, Vgs | 1.25 Ohm @ 500mA, 10V |
| VGS (th) (Max) @ Id | 2.5V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 0.6nC @ 4.5V |
| Eingabekapazität (Ciss) (Max) @ Vds | 30pF @ 25V |
| Antriebsspannung (Max Rds On, Min Rds On) | 4.5V, 10V |
| Vgs (Max) | ±20V |
| Verpackung | Tape & Reel (TR) |

SI1022R-T1-GE3 ist neu im Original, Suche SI1022R-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI1022R-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI1022R-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|--|
|  SI1022R-T1-E3 VISHAY SI1022R-T1-E3 VISHAY |  SI1022R VISHAY SI1022R VISHAY |  SI1022R-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 330MA SC-75A |  SI1022R-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 60V 330MA SC-75A |
|  SI1023-A-GM Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA |  SI1023-A-GMR Energy Micro (Silicon Labs) IC RF TXRX+MCU ISM<1GHZ 85-VFLGA |  SI1022R-T1 VISHAY SI1022R-T1 VISHAY |  SI1022R-T1-E3 Vishay / Siliconix MOSFET N-CH 60V 330MA SC-75A |

heiße Teile

Mehr

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|-----------------|-----------------|-----------------|----------------|----------------|
| SI1013CX-T1-GE3 | SI1013R-T1 | SI1013R-T1-E3 | SI1013R-T1-E3 | SI1013R-T1-GE3 |
| SI1013R-T1-GE3 | SI1013X-T1 | SI1013X-T1-E3 | SI1013X-T1-E3 | SI1013X-T1-GE3 |
| SI1013X-T1-GE3 | SI1016CX-T1-GE3 | SI1016CX-T1-GE3 | SI1016X-T1-E3 | SI1016X-T1-E3 |
| SI1016X-T1-GE3 | SI1016X-T1-GE3 | SI1016X2-T1-GE3 | SI1021R-T1 | SI1021R-T1-E3 |
| SI1021R-T1-E3 | SI1022R-T1 | SI1022R-T1-E3 | SI1022R-T1-E3 | SI1022R-T1-GE3 |
| SI1022R-T1-E3 | SI1023CX-T1-GE3 | SI1023CX-T1-GE3 | SI1023X-T1 | SI1023X-T1-E3 |
| SI1023X-T1-E3 | SI1023X-T1-GE3 | SI1023X-T1-GE3 | SI1024-T1 | SI1024X-T1 |
| SI1024X-T1-E3 | SI1024X-T1-E3 | SI1024X-T1-GE3 | SI1024X-T1-GE3 | SI1024X-T1-GE3 |
| SI1025X-T1 | SI1025X-T1-E3 | SI1025X-T1-E3 | SI1026X-T1 | SI1026X-T1-E3 |
| SI1026X-T1-E3 | SI1026X-T1-GE3 | SI1026X-T1-GE3 | SI1028X-T1-GE3 | SI1028X-T1-GE3 |

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